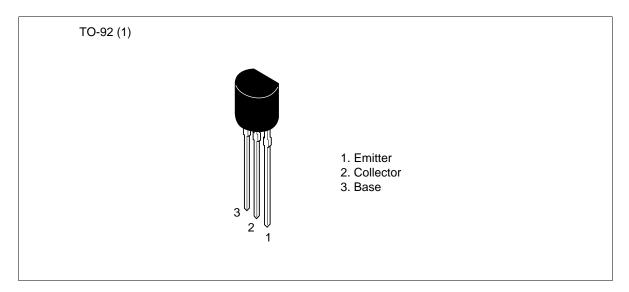
Silicon PNP Epitaxial

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Application

- Low frequency low noise amplifier
- Complementary pair with 2SC2855 and 2SC2856

Outline





Absolute Maximum Ratings (Ta = 25° C)

Item	Symbol	2SA1190	2SA1191	Unit
Collector to base voltage	V _{CBO}	-90	-120	V
Collector to emitter voltage	V _{CEO}	-90	-120	V
Emitter to base voltage	V _{EBO}	-5	-5	V
Collector current	I _c	-100	-100	mA
Emitter current	Ι _Ε	100	100	mA
Collector power dissipation	Pc	400	400	mW
Junction temperature	Tj	150	150	°C
Storage temperature	Tstg	-55 to +150	-55 to +150	°C

Electrical Characteristics (Ta = 25°C)

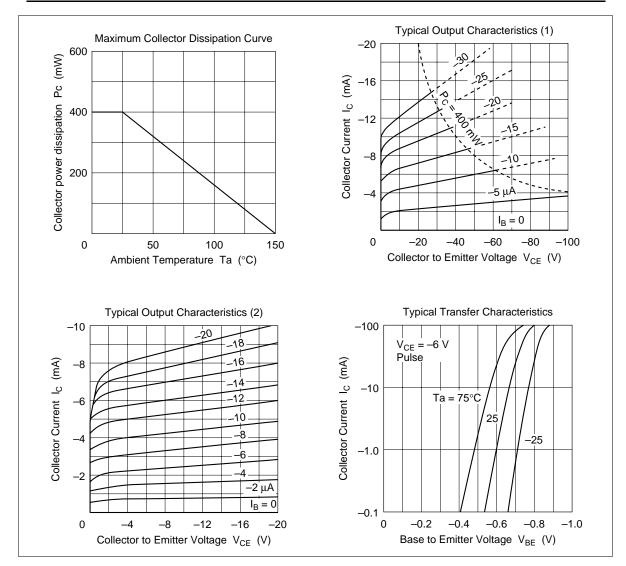
		2SA1	190		2SA1191				
Item	Symbol	Min	Тур	Max	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{\rm (BR)CBO}$	-90	_	_	-120	_	_	V	$I_{c} = -10 \ \mu A, I_{E} = 0$
Collector to emitter breakdown voltage	$V_{\scriptscriptstyle (BR)CEO}$	-90	_	—	-120	—	—	V	$I_c = -1 \text{ mA}, \text{ R}_{BE} = \infty$
Emitter to base breakdown voltage	$V_{\scriptscriptstyle (BR)EBO}$	-5	_	—	-5	—	—	V	$I_{\rm E} = -10 \ \mu A, \ I_{\rm C} = 0$
Collector cutoff current	I _{CBO}	_		-0.1	—	—	-0.1	μΑ	$V_{_{CB}} = -70 \text{ V}, \text{ I}_{_{E}} = 0$
Emitter cutoff current	I _{EBO}	—		-0.1	—	—	-0.1	μΑ	$V_{EB} = -2 V, I_{C} = 0$
DC current trnsfer ratio	$h_{\rm FE}^{*1}$	250	_	800	250	—	800		$V_{ce} = -12 V,$ $I_c = -2 mA^{*2}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	-0.05	-0.15	_	-0.05	-0.15	V	$I_{c} = -10 \text{ mA},$ $I_{B} = -1 \text{ mA}^{*2}$
Base to emitter saturation voltage	$V_{\text{BE(sat)}}$	—	-0.7	-1.0	_	-0.7	-1.0	V	_
Gain bandwidth product	f _T	_	130	_	_	130	_	MHz	$V_{ce} = -6 V,$ $I_{c} = -10 mA$
Collector output capacitance	Cob	—	3.2	—	—	3.2	—	pF	$V_{CB} = -10 \text{ V}, \text{ I}_{E} = 0,$ f = 1 MHz
Noise figure	NF	_	0.15	1.5	—	0.15	1.5	dB	$V_{ce} = -6 V,$ $I_c = -0.1 mA,$ $R_g = 10 k\Omega$ f = 1 kHz
		_	0.2	2.0	—	0.2	2.0	dB	$V_{ce} = -6 V,$ $I_c = -0.1 mA,$ $R_g = 10 k\Omega$ f = 10 Hz
Noise voltage reffered to input	e _n	—	0.7	_	_	0.7	_	nV/ √Hz	$V_{_{CB}} = -6 V,$ $I_{_{C}} = -10 mA,$ Rg = 0, f = 1 kHz

Pulse test

D

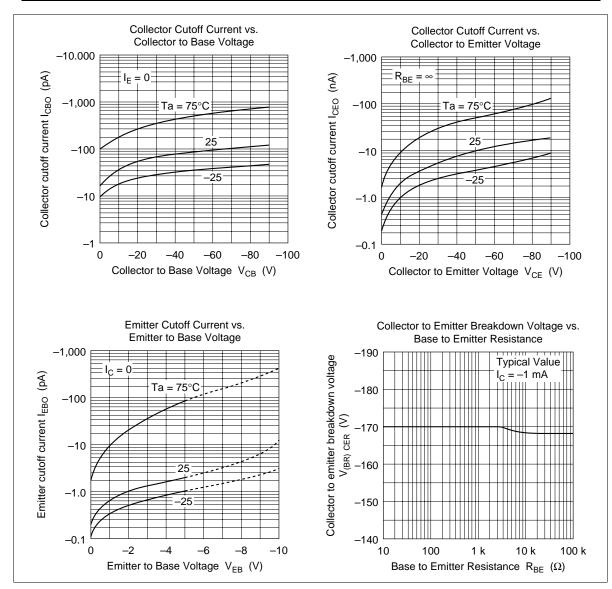
250 to 500 400 to 800

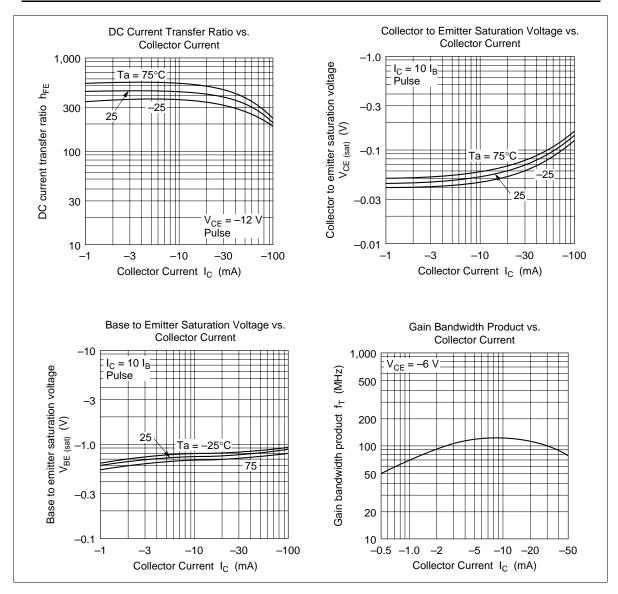
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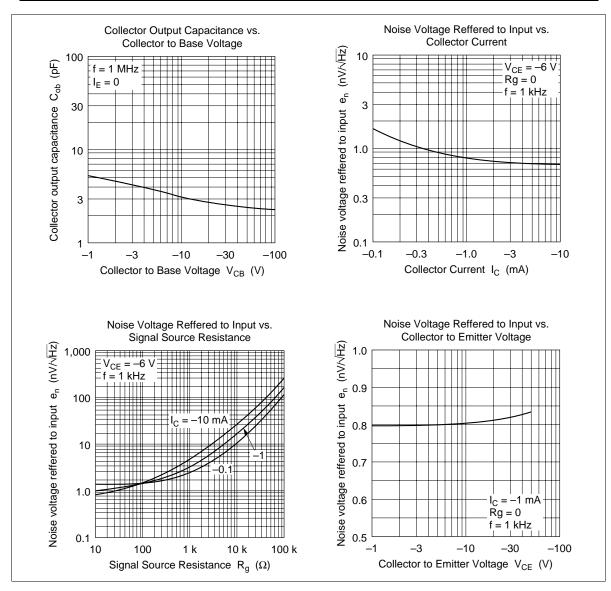


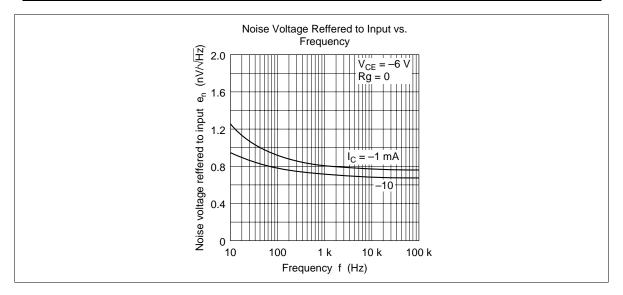
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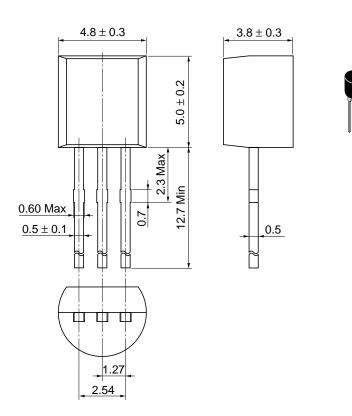








Unit: mm



Hitachi Code	TO-92 (1)
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.25 g

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